2SB0940 (2SB940), **2SB0940A** (2SB940A)

Silicon PNP epitaxial planar type

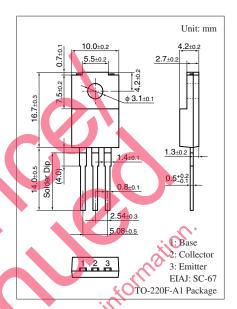
For power amplification For TV vertical deflection output Complementary to 2SD1264, 2SD1264A

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- Large collector power dissipation P_C
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Er	V_{CBO}	-200	V	
Collector-emitter voltage	2SB0940	V _{CEO}	-150	V
(Base open)	2SB0940A		-180	
Emitter-base voltage (Coll	V_{EBO}	-6	V	
Collector current	$I_{\mathbb{C}}$	-2	A	
Peak collector current	I_{CP}	-3	A	
Collector power		P_{C}	30	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		T_{j}	150	°C
Storage temperature		T_{stg}	-55 to +150	°C



■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

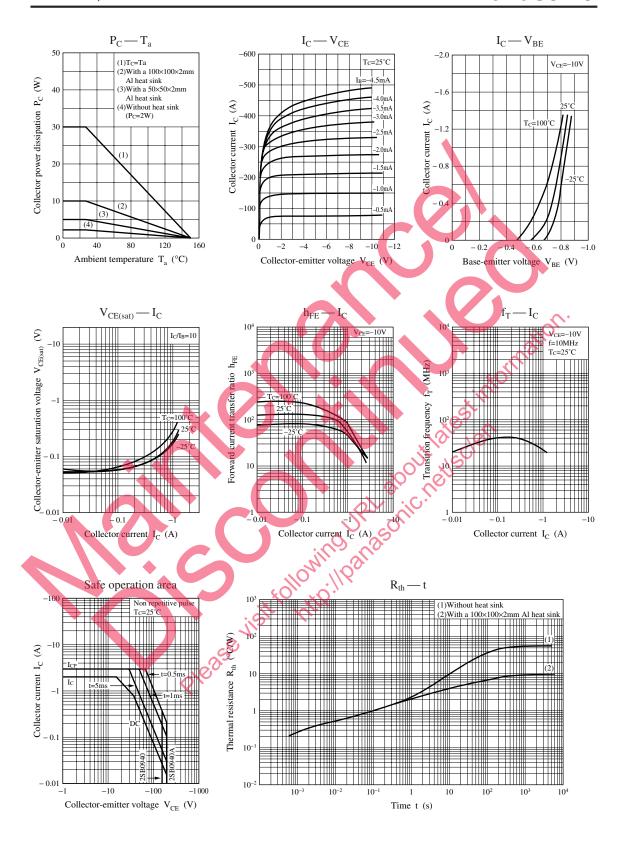
Collector current	$I_{\mathbb{C}}$	-2 A	*	16.			
Peak collector current	I _{CP}	-3 A	S				
Collector power	P _C	30 W	XV (25			
dissipation $T_A = 25^{\circ}C$							
Junction temperature T _j 150 °C							
Storage temperature $T_{stg} = -55 \text{ to } +150 \text{ °C}$							
Collector current Peak collector current I_{CP} I							
Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -50 \mu{\rm A}, I_{\rm E} = 0$	-200			V	
Collector-emitter voltage 2SB0940	V _{CEO}	$I_{C} = -5 \text{ mA}, I_{B} = 0$	-150			V	
(Base open) 2SB0940A		L'IO KILO	-180				
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -500 \mu\text{A}, I_{\rm C} = 0$	-6			V	
Base-emitter voltage	VBE	$V_{CE} = -10 \text{ V}, I_{C} = -400 \text{ mA}$			-1	V	
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -200 \text{ V}, I_E = 0$			-50	μΑ	
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -4 \text{ V}, I_C = 0$			-50	μΑ	
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	60		240	_	
	h _{FE2}	$V_{CE} = -10 \text{ V}, I_{C} = -400 \text{ mA}$	50				
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1	V	
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	Р		
$h_{\rm FE1}$	60 to 140	100 to 240		

Note) The part numbers in the parenthesis show conventional part number.



2 SJD00021BED

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